

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4864	257/758	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/21 03:05
S1	39	(semiconductor or die or chip or IC) and dummy near via and dummy near (wirings or conductive or pattern)	USPAT	OR	ON	2004/12/23 14:13
S2	46	(semiconductor or die or chip or IC) and dummy near via and dummy near (wirings or conductive or pattern)	USPAT; JPO	OR	ON	2004/12/22 01:10
S3	0	"11350284"	JPO	OR	ON	2004/12/22 01:11
S4	0	"110350284"	JPO	OR	ON	2004/12/22 01:11
S5	0	"11350284"	JPO	OR	ON	2004/12/22 01:11
S6	1867	dielectric near constant with (silicon near dioxide)	USPAT	OR	OFF	2004/12/23 17:44
S7	1887	dielectric near constant with (silicon near nitride)	USPAT	OR	OFF	2004/12/22 02:06
S8	358	dielectric near constant with (SOG)	USPAT	OR	OFF	2004/12/22 02:06
S9	6167	dimension with via	USPAT	OR	ON	2004/12/22 13:38
S10	7164	(dimension or (cross-sectional or cross near sectional) near area) with via	USPAT	OR	ON	2004/12/22 13:39
S11	1065	((cross-sectional or cross near sectional) near area) with via	USPAT	OR	ON	2004/12/22 13:40
S12	7	S11 and ((cross-sectional or cross near sectional) near area) with via with normal	USPAT	OR	ON	2004/12/22 13:41
S13	0	( chip or die) and ((cross-sectional or cross near sectional) near area) with via with normal	USPAT	OR	ON	2004/12/22 13:41
S14	219	( chip or die) and ((cross-sectional or cross near sectional) near area) with via	USPAT	OR	ON	2004/12/22 14:09
S15	0	S14 and via with "microns.sub.-2"	USPAT	OR	ON	2004/12/22 14:21
S16	0	S14 and via with "\$.sub.-2"	USPAT	OR	ON	2004/12/22 13:50
S17	0	S14 and via with "sub.-2"	USPAT	OR	ON	2004/12/22 13:50
S18	0	S14 and via with "-2"	USPAT	OR	ON	2004/12/22 13:50

S19	6	"5,023,850".pn. or "4,551,857".pn. or "4,320,756".pn. or "5,934,226".pn. or "4,905,406".pn. or "5,901,666".pn.	USPAT	OR	ON	2004/12/22 13:55
S20	42	S14 and diameter with via	USPAT	OR	ON	2004/12/22 14:10
S21	0	S14 and via with "microns.sup.-2"	USPAT	OR	ON	2004/12/22 14:24
S22	0	S14 and via with ".sup.-2"	USPAT	OR	ON	2004/12/22 14:21
S23	0	S14 and via with "-2"	USPAT	OR	ON	2004/12/22 14:21
S24	0	S14 and via with ".sup."	USPAT	OR	ON	2004/12/22 14:21
S25	0	S11 and via with "microns.sup.-2"	USPAT	OR	ON	2004/12/22 14:22
S26	0	S11 and via with ".sup.-2"	USPAT	OR	ON	2004/12/22 14:22
S27	0	S11 and via same ".sup.-2"	USPAT	OR	ON	2004/12/22 14:22
S28	0	S11 and vias same ".sup.-2"	USPAT	OR	ON	2004/12/22 14:22
S29	0	".sup.-2"	USPAT	OR	ON	2004/12/22 14:22
S30	0	".sup.-2"	USPAT	OR	ON	2004/12/22 14:24
S31	0	"mu.m.sup.-2"	USPAT	OR	ON	2004/12/22 14:24
S32	0	"mu.m.sup."	USPAT	OR	ON	2004/12/22 14:24
S33	296570	"mu.m"	USPAT	OR	ON	2004/12/22 14:24
S34	35	S14 and via with (microns or "mu.m")	USPAT	OR	ON	2004/12/22 19:36
S35	5041	257/758	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/22 19:57
S36	3612	257/774	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/22 20:06
S37	1164	257/775	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/22 20:18
S38	1262	257/776	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/22 22:11

S39	2755	257/700	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/22 22:11
S40	14	(semiconductor or die or chip or IC) and dummy near (wirings or conductive or pattern) with SOG	USPAT	OR	ON	2004/12/23 18:44
S41	4	(semiconductor or die or chip or IC) and dummy near (wirings or conductive or pattern) with ground near (layer or film or plane)	USPAT	OR	ON	2004/12/23 17:51
S42	18	(semiconductor or die or chip or IC) and dummy near (wirings or conductive or pattern or layer or film) with SOG	USPAT	OR	ON	2004/12/23 15:07
S43	1132	dielectric near constant with (polyimide)	USPAT	OR	OFF	2004/12/23 17:44
S44	0	(semiconductor or die or chip or IC) and dummy near (wirings or conductive or pattern) with (xerogel or BCB)	USPAT	OR	ON	2004/12/23 17:51
S45	8	(semiconductor or die or chip or IC) and dummy near (wirings or conductive or pattern) and (xerogel or BCB) with (insulat\$3 or dielectric)	USPAT	OR	ON	2004/12/23 17:52
S46	16	(semiconductor or die or chip or IC) and dummy near (wirings or conductive or pattern or film or layer) and (xerogel or BCB) with (insulat\$3 or dielectric)	USPAT	OR	ON	2004/12/23 18:01
S47	2	"09315682"	JPO	OR	ON	2004/12/23 18:02
S48	2	"10037673"	JPO	OR	ON	2004/12/23 18:02
S49	0	(semiconductor or die or chip or IC) and dummy near (vias or contact near hole) with slit	USPAT	OR	ON	2004/12/23 18:45
S50	2	(semiconductor or die or chip or IC) and dummy with (vias or contact near hole) with slit	USPAT	OR	ON	2004/12/23 18:45
S51	1	"6319809".pn.	USPAT	OR	OFF	2005/06/20 13:04
S52	5	257/758 and (dummies or dummy) and coplanar with (interconnect or wiring)	USPAT	OR	ON	2005/06/20 14:00
S53	49	257/758 and coplanar with (interconnect or wiring)	USPAT	OR	ON	2005/06/20 14:00

S54	305	damascene and (dummy or dummies) and (dielectric or insulat\$3) with (SOG or glass or silicon)	USPAT	OR	ON	2005/06/20 15:27
S55	22	damascene and (dummy or dummies) near (via or hole) and (dielectric or insulat\$3) with (SOG or glass or silicon)	USPAT	OR	ON	2005/06/20 14:26
S56	283	S54 not S55	USPAT	OR	ON	2005/06/20 14:32
S57	29	damascene and (dummy or dummies) near (via or hole)	USPAT	OR	ON	2005/06/20 15:27
S58	83	damascene and (dummy or dummies) with (via or hole)	USPAT	OR	ON	2005/06/20 19:41
S59	818	dielectric near constant with ("BCB" or "HSQ" or "SiOF")	USPAT	OR	ON	2005/06/20 16:32
S60	329	dielectric near constant with ("BCB" )	USPAT	OR	ON	2005/06/20 17:07
S61	82	damasc\$3 and (dummy or dummies) with (via or hole)	USPAT	OR	ON	2005/06/20 16:42
S62	366	damasc\$3 and (dummy or dummies)	USPAT	OR	ON	2005/06/20 20:30
S63	57	dielectric near constant with (helium )	USPAT	OR	ON	2005/06/20 18:57
S64	1	"5948928".PN.	USPAT; USOCR	OR	OFF	2005/06/20 17:29
S65	1	"20020160599"	US-PGPUB; USPAT	OR	ON	2005/06/20 18:57
S66	47	damascene and (dummy or dummies) and (dielectric or insulat\$3) with ("SOG" or parylene or xerogel)	USPAT	OR	ON	2005/06/20 20:30
S67	361	damascene and (dummy or dummies)	USPAT	OR	ON	2005/06/20 20:30
S68	501	damasc\$3 and (dummy or dummies)	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 21:14
S69	366	damasc\$3 and (dummy or dummies)	USPAT	OR	ON	2005/06/20 21:14
S70	1	"20050035457"	US-PGPUB; USPAT; JPO	OR	OFF	2005/06/21 00:27
S71	1	"20050035457" and dummy with "10" with times	US-PGPUB; USPAT; JPO	OR	OFF	2005/06/20 21:33

S72	1	"6717268".pn. or "2001429552".pn.	US-PGPUB; USPAT; JPO	OR	OFF	2005/06/20 21:34
S73	1	"6717268".pn. or "2001429552".pn.	US-PGPUB; USPAT; JPO	OR	ON	2005/06/20 21:34
S74	1	"6717268".pn. or "2001429552".pn. and dummy	US-PGPUB; USPAT; JPO	OR	ON	2005/06/20 21:35
S75	1	"6717268".pn. or "2001429552".pn. and dummy	US-PGPUB; USPAT; JPO	OR	ON	2005/06/20 21:37
S76	14382	( dummy or dummies) and (semiconductor or die or dice or chip or IC)	USPAT	OR	ON	2005/06/20 21:38
S77	2865	( dummy or dummies) with (via ro hole or plug or interconnect\$3 or pattern) and (semiconductor or die or dice or chip or IC)	USPAT	OR	ON	2005/06/20 21:38
S78	1474	( dummy or dummies) with (via ro hole ) and (semiconductor or die or dice or chip or IC)	USPAT	OR	ON	2005/06/20 21:56
S79	97	( dummy or dummies) with (via ro hole ) and (semiconductor or die or dice or chip or IC) and cap	USPAT	OR	ON	2005/06/20 22:04
S80	90	( dummy or dummies) with (via ro hole ) and (semiconductor or die or dice or chip or IC) and 257/758	USPAT	OR	ON	2005/06/20 22:18
S81	775	( dummy or dummies) with (via ro hole ) and (semiconductor or die or dice or chip or IC) and (multi\$5)	USPAT	OR	ON	2005/06/20 22:18
S82	1	"20050035457" and vias with cap	US-PGPUB; USPAT; JPO	OR	ON	2005/06/21 00:27
S83	368	damasc\$3 and (dummy or dummies)	USPAT	OR	ON	2005/06/21 01:26
S84	124	dual near damasc\$3 and (dummy or dummies)	USPAT	OR	ON	2005/06/21 01:56
S85	0	(dummy or dummies) with diameter with "10" near times with (vias or via or hole)	USPAT	OR	ON	2005/06/21 03:04